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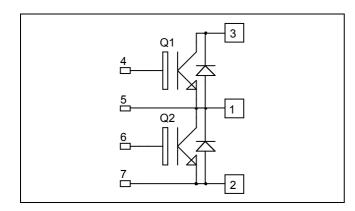






Phase leg Trench + Field Stop IGBT3 Power Module





Application

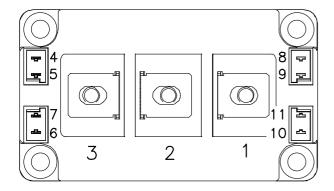
- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant



Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1700	V
T	Continuous Collector Current	$T_C = 25^{\circ}C$	310	
$I_{\rm C}$	Continuous Conector Current	$T_C = 80$ °C	200	A
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	400	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	$T_C = 25$ °C	1250	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125$ °C	400A@1650V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1700V$				3	mA
V _{CE(on)}	Collector Emitter on Voltage	$V_{GE} = 15V$ $T_{j} = 25^{\circ}C$ $T_{j} = 125^{\circ}C$	$T_j = 25$ °C		2.0	2.5	V
			$T_j = 125$ °C		2.4		v
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 8 \text{ mA}$		5.2	5.8	6.4	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

Dynamic Characteristics

•	Characteristic	Test Conditions	M	fin Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V, V_{CE} = 25V$		18		nF
C_{res}	Reverse Transfer Capacitance	f = 1MHz		0.6		ШГ
Q_{G}	Gate charge	V _{GE} =±15V, I _C =200A V _{CE} =900V		2.3		μС
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (2	5°C)	280		ns
T _r	Rise Time	$V_{GE} = \pm 15V$		80		
T _{d(off)}	Turn-off Delay Time	$V_{\text{Bus}} = 900V$ $I_{\text{C}} = 200A$		850		
T_{f}	Fall Time	$R_G = 6.8\Omega$		120		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (1	25°C)	300		
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$		100		
T _{d(off)}	Turn-off Delay Time	$V_{\text{Bus}} = 900V$ $I_{\text{C}} = 200A$		1000		ns
T_{f}	Fall Time	$R_G = 6.8\Omega$		200		
Eon	Turn On Energy	$V_{GE} = \pm 15V$ $T_i =$	25°C	58		
Lon	Turn On Energy		125°C	78		mJ
E_{off}	Turn Off Energy		25°C	43		1113
L'off	Turn On Energy	$R_G = 6.8\Omega$ $T_i =$	125°C	63		
I_{sc}	Short Circuit data	$V_{GE} \le 15V$; $V_{Bus} = 100$ $t_p \le 10 \mu s$; $T_i = 125 ^{\circ}C$	0V	800		A

Reverse diode ratings and characteristics

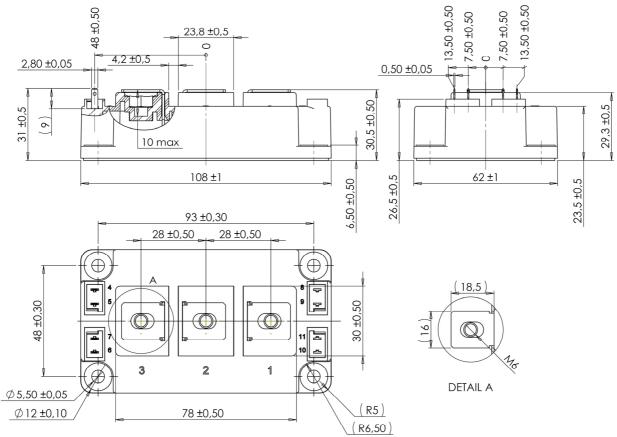
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1700			V
I_{RRM}	Maximum Reverse Leakage Current	V _R =1700V	$T_j = 25$ °C			750	μA
radvi	2	K	$T_{j} = 125^{\circ}C$			1000	•
I_{F}	DC Forward Current		$Tc = 80^{\circ}C$		200		A
$V_{\rm F}$	Diode Forward Voltage	$I_F = 200A$	$T_j = 25^{\circ}C$		1.8	2.2	V
VF	Diode Forward Voltage		$T_i = 125$ °C		1.9		v
t_{rr}	Reverse Recovery Time		$T_j = 25^{\circ}C$		385		ng
	Reverse Recovery Time	2004	$T_j = 125$ °C		490		ns
Q _{rr}	Daviana Bassyany Change	$I_F = 200A$ $V_R = 900V$	$T_j = 25$ °C		56		C
	Reverse Recovery Charge	$di/dt = 3200 \text{ A/\mu s}$	$T_{j} = 125^{\circ}C$		92		μС
E _{rr}	Reverse Recovery Energy		$T_j = 25$ °C		24		mJ
\mathbf{L}_{rr}			$T_i = 125^{\circ}C$		48		1113



Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R_{thJC}	L Junction to Case Thermal Resistance		IGBT			0.10	°C/W
T _{th} JC			Diode			0.16	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range					150	
T_{STG}	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature			-40		125	
Torque	Mounting torque	For terminals	M6	3		5	N.m
		To Heatsink	M6	3		5	19.111
Wt	Package Weight					350	g

D3 Package outline (dimensions in mm)

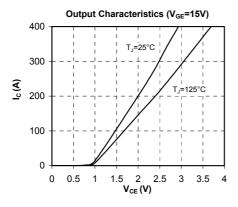


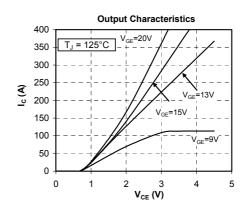
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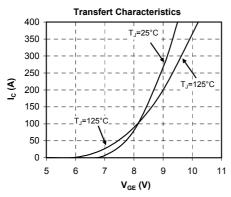
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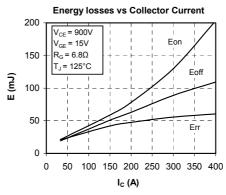


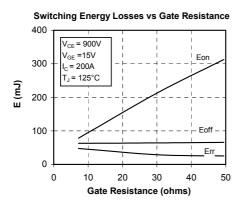
Typical Performance Curve

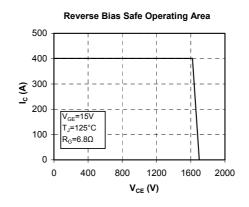


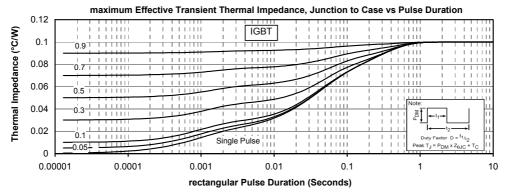




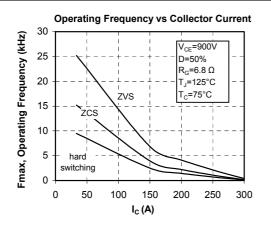


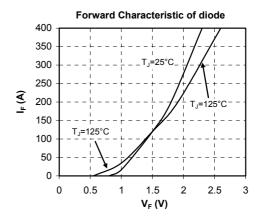


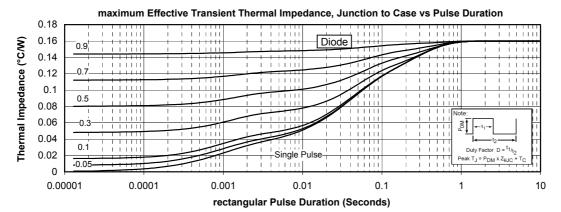














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